美浦森半导体
M s e m i t e k

RoHS
LEAD FREE

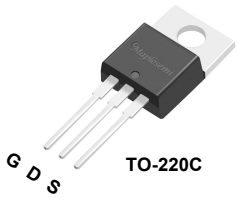
SLP12N70S / SLF12N70S
700V N-Channel MOSFET

General Description

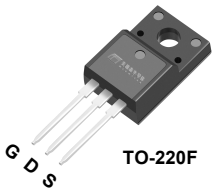
This Power MOSFET is produced using Msemitek's advanced planar stripe DMOS technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

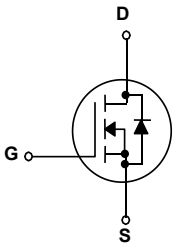
- N-Channel:700V 12A
  $R_{DS(on)Typ}$= 680mΩ@V_{GS} = 10 V
- Low gate charge (typical 90 nC)
- Very Low On-resistance $R_{DS(ON)}$
- Low Crss
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-220C



TO-220F



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter	SLP12N70S / SLF12N70S	Units
V_{DSS}	Drain-Source Voltage	700	V
I_D	Drain Current - Continuous (T_C = 25℃)	12	A
	- Continuous (T_C = 100℃)	7.6	A
I_{DM}	Drain Current - Pulsed (Note 1)	48	A
V_{GSS}	Gate-Source Voltage	±30	V
E_{AS}	Single Pulsed Avalanche Energy	759	mJ
P_D	Power Dissipation (T_C = 25℃)	38	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.87	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	℃
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	℃

* Drain current limited by maximum junction temperature.

Package Marking

Part Number	Top Marking	Package	Packing Method	MOQ	QTY
SLP12N70S	SLP12N70S	TO-220C	Tube	1000	5000
SLF12N70S	SLF12N70S	TO-220F	Tube	1000	5000

Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 uA	700	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} =700 V, V_{GS} = 0 V	--	--	1	uA
		V_{DS} = 560V, T_C = 125℃	--	--	10	uA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} =30V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 uA	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D =6A	--	0.68	0.90	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} =25 V, V_{GS} = 0 V, f = 1.0 MHz	--	2150	-	pF
C_{oss}	Output Capacitance		--	143	-	pF
C_{rss}	Reverse Transfer Capacitance		--	3.74	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}= 350V, R_G = 25Ω ,I_D=12A	--	30	--	ns
t_r	Turn-On Rise Time		--	42.2	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	135	--	ns
t_f	Turn-Off Fall Time		--	50	--	ns
Q_g	Total Gate Charge	V_{DS} = 560V, I_D =12A, V_{GS} = 10V	--	51	--	nC
Q_{gs}	Gate-Source Charge		--	11.8	--	nC
Q_{gd}	Gate-Drain Charge		--	20.5	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	12	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	48	A
V_{SD}	Drain to Source Diode Forward Voltage,V_{GS} = 0V, I_{SD} =12A,T J = 25℃		--	--	1.2	V
t_{rr}	Reverse Recovery Time &T_J = 25°C, IF = 20A di/dt = 100A/μs		--	556	-	nS
Q_{rr}	Reverse Recovery Charge & T_J = 25°C, IF = 20A di/dt = 100A/μs		--	4.9	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: T_J =25℃, V_{DD} =50V, V_G =10V, R G =25Ω, L=0.5mH, I_{AS} =12A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

N- Channel Typical Characteristics

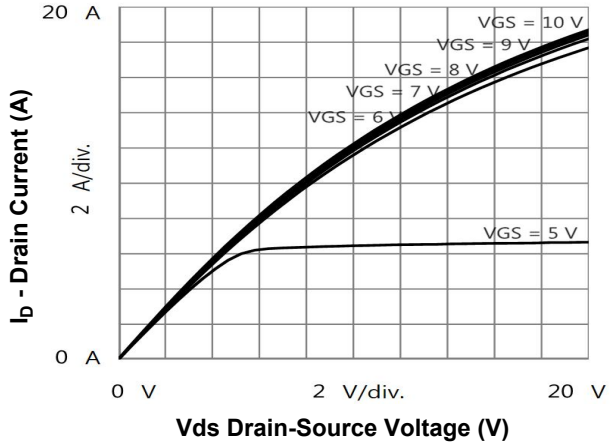


Figure 1. On-Region Characteristics

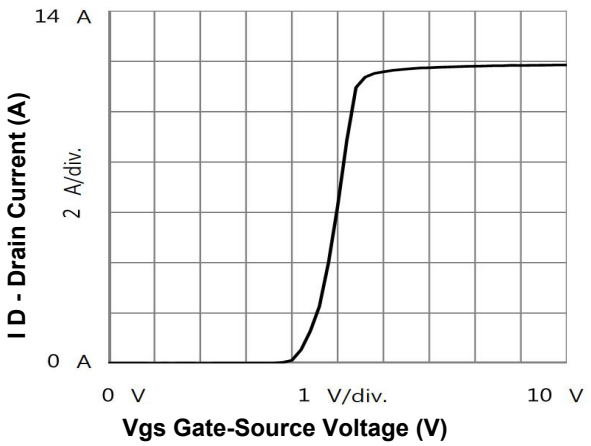


Figure 2. Transfer Characteristics

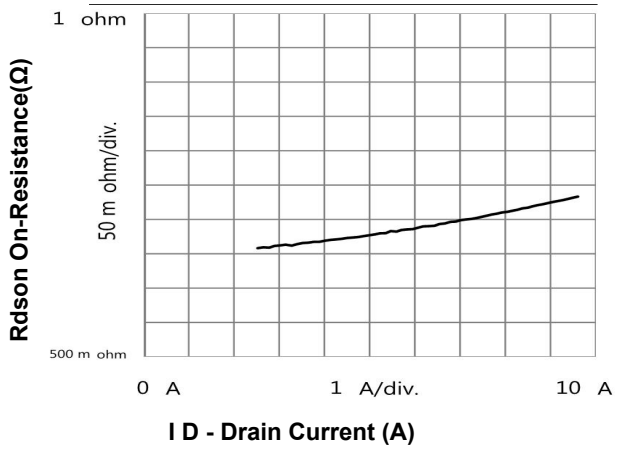


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

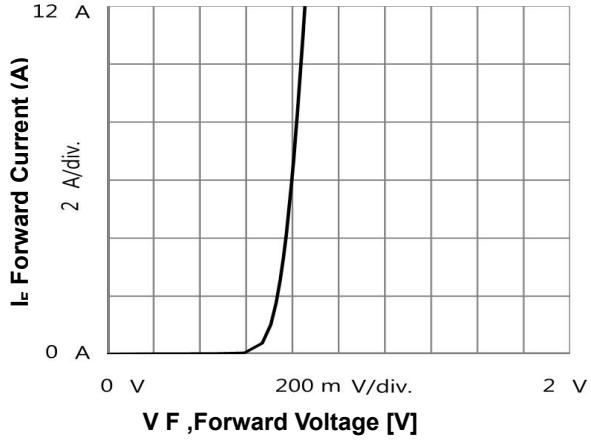


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

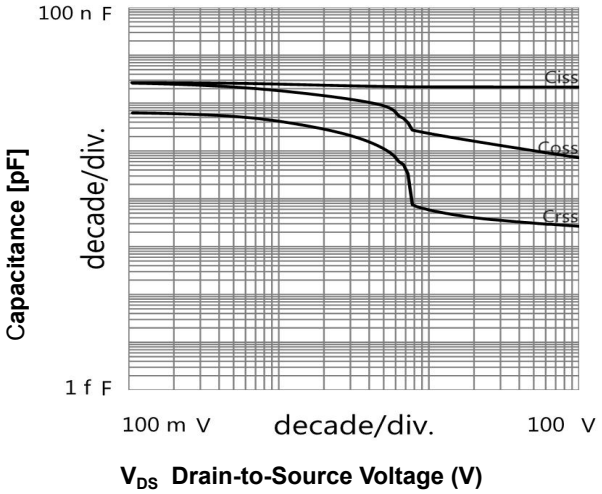


Figure 5. Capacitance Characteristics

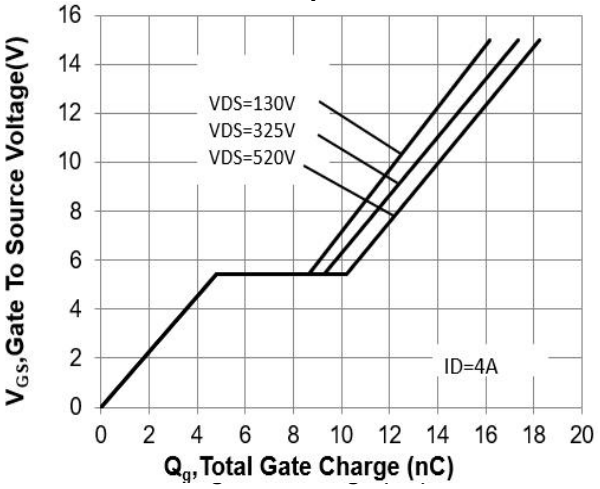


Figure 6. Gate Charge Characteristics

N- Channel Typical Characteristics (Continued)

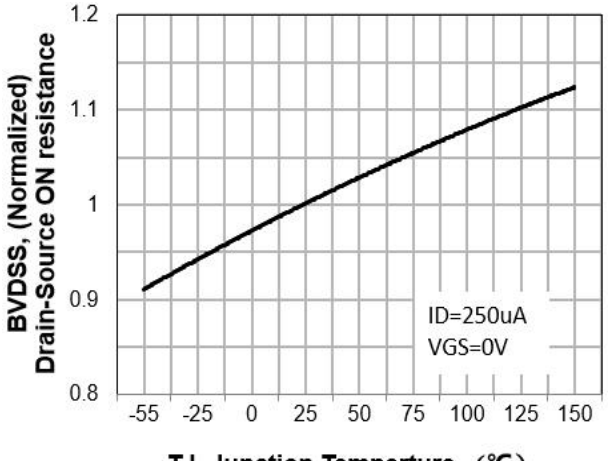


Figure 7. Breakdown Voltage Variation vs Temperature

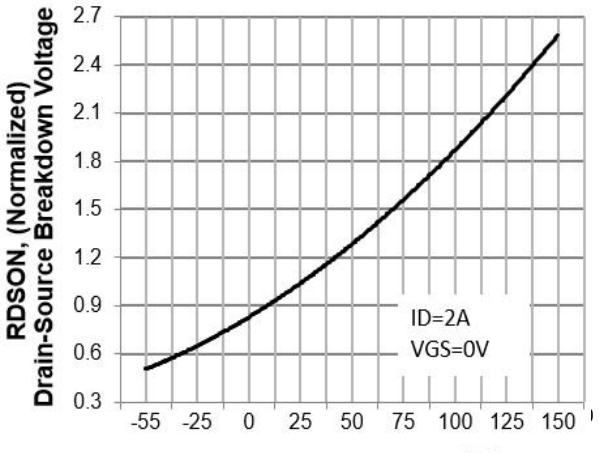


Figure 8. On-Resistance Variation vs Temperature

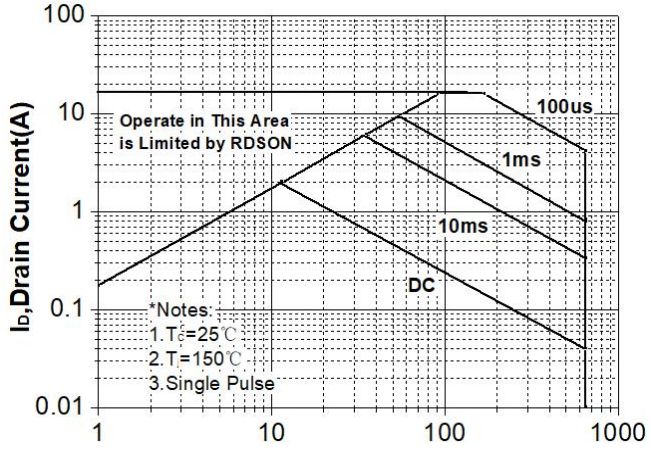


Figure 9. Maximum Safe Operating Area

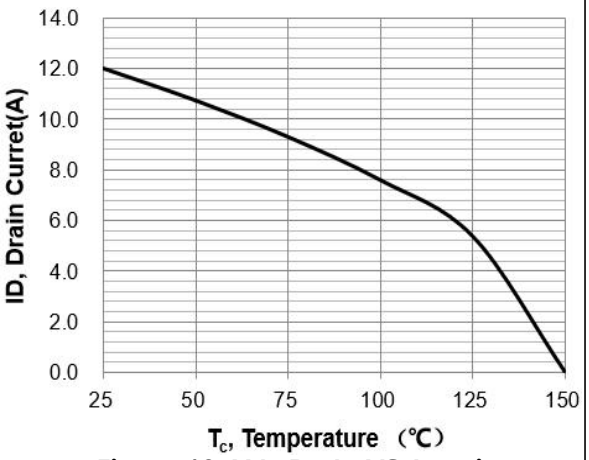


Figure 10. Vds Drain VS Junction Temperature

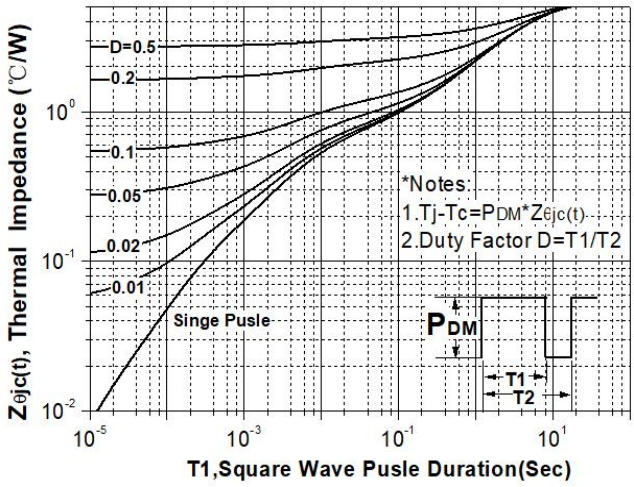
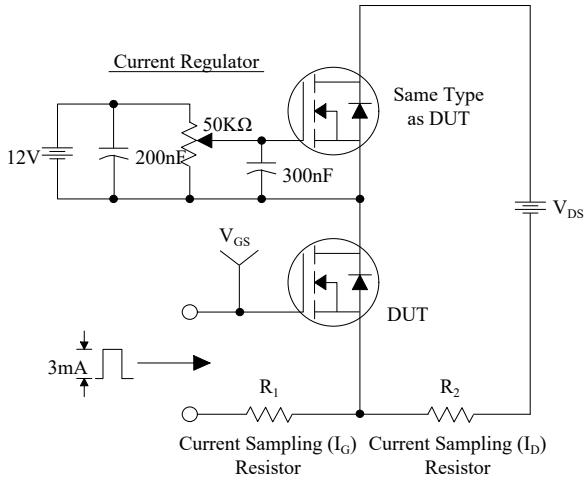
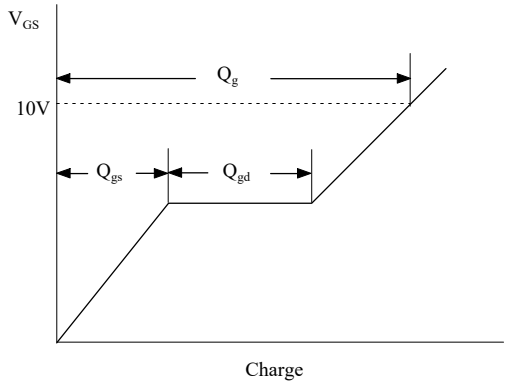


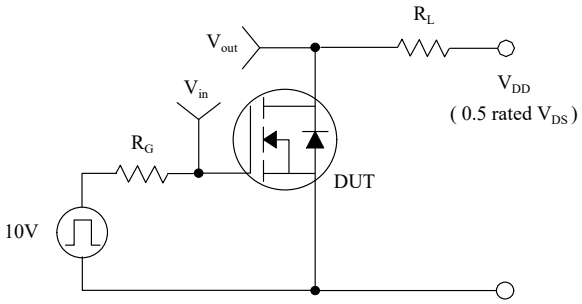
Figure 11. Transient Thermal Response Curve

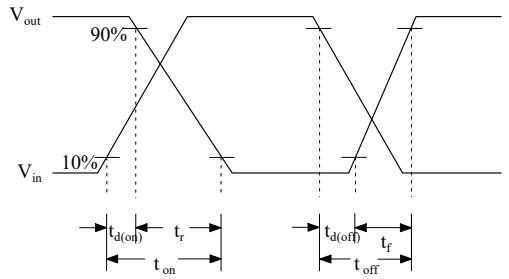
Gate Charge Test Circuit & Waveform



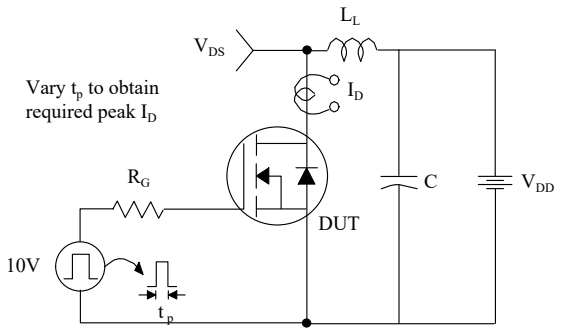


Resistive Switching Test Circuit & Waveforms

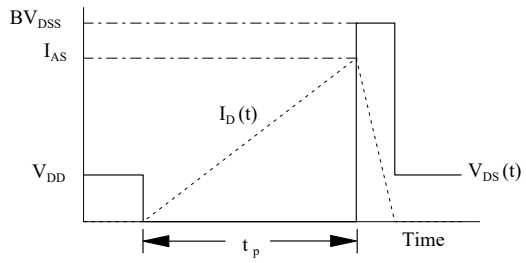




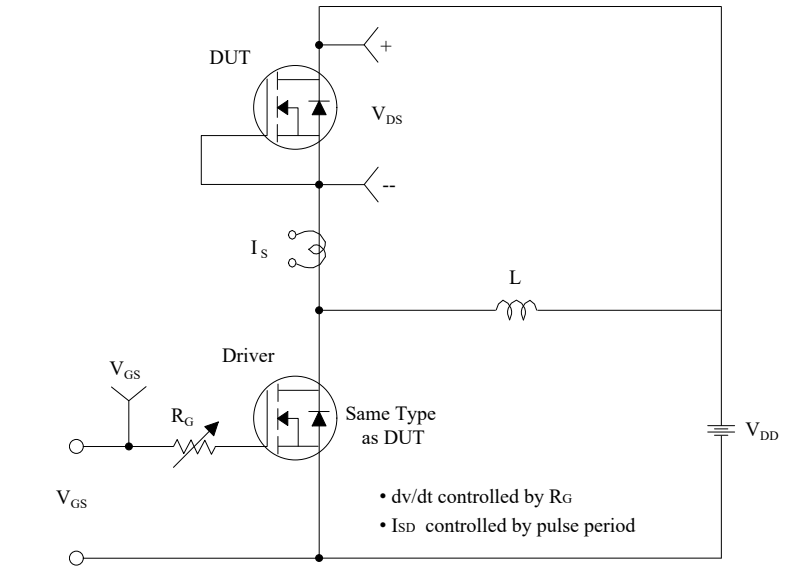
Unclamped Inductive Switching Test Circuit & Waveforms

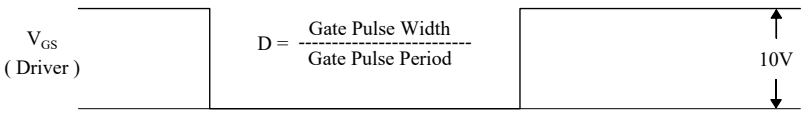


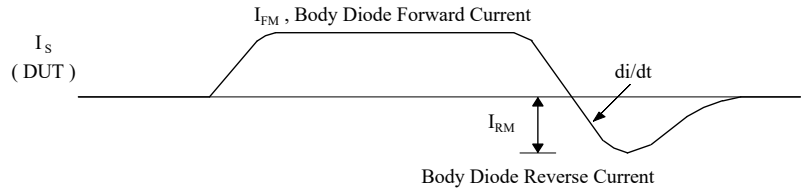
$$E_{AS} = \frac{1}{2} L_L I_{AS}^2$$

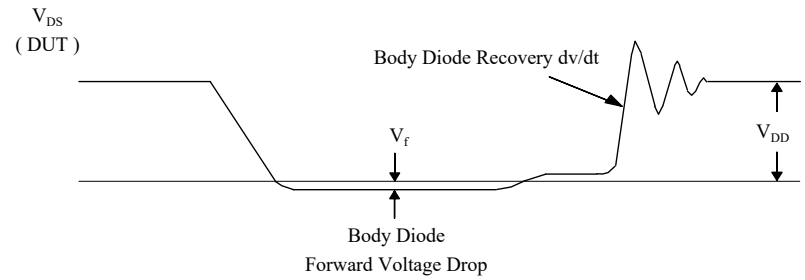


Peak Diode Recovery dv/dt Test Circuit & Waveforms

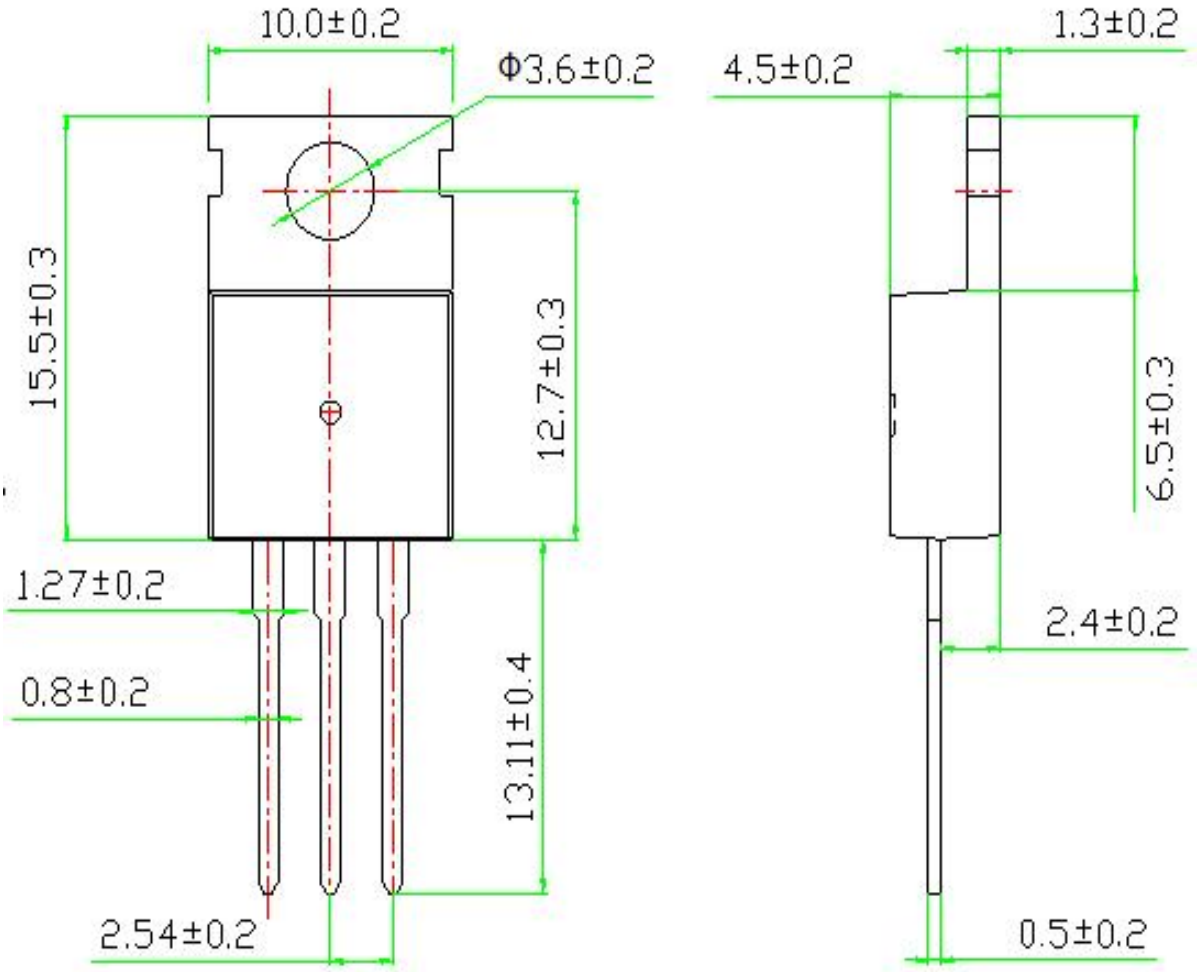




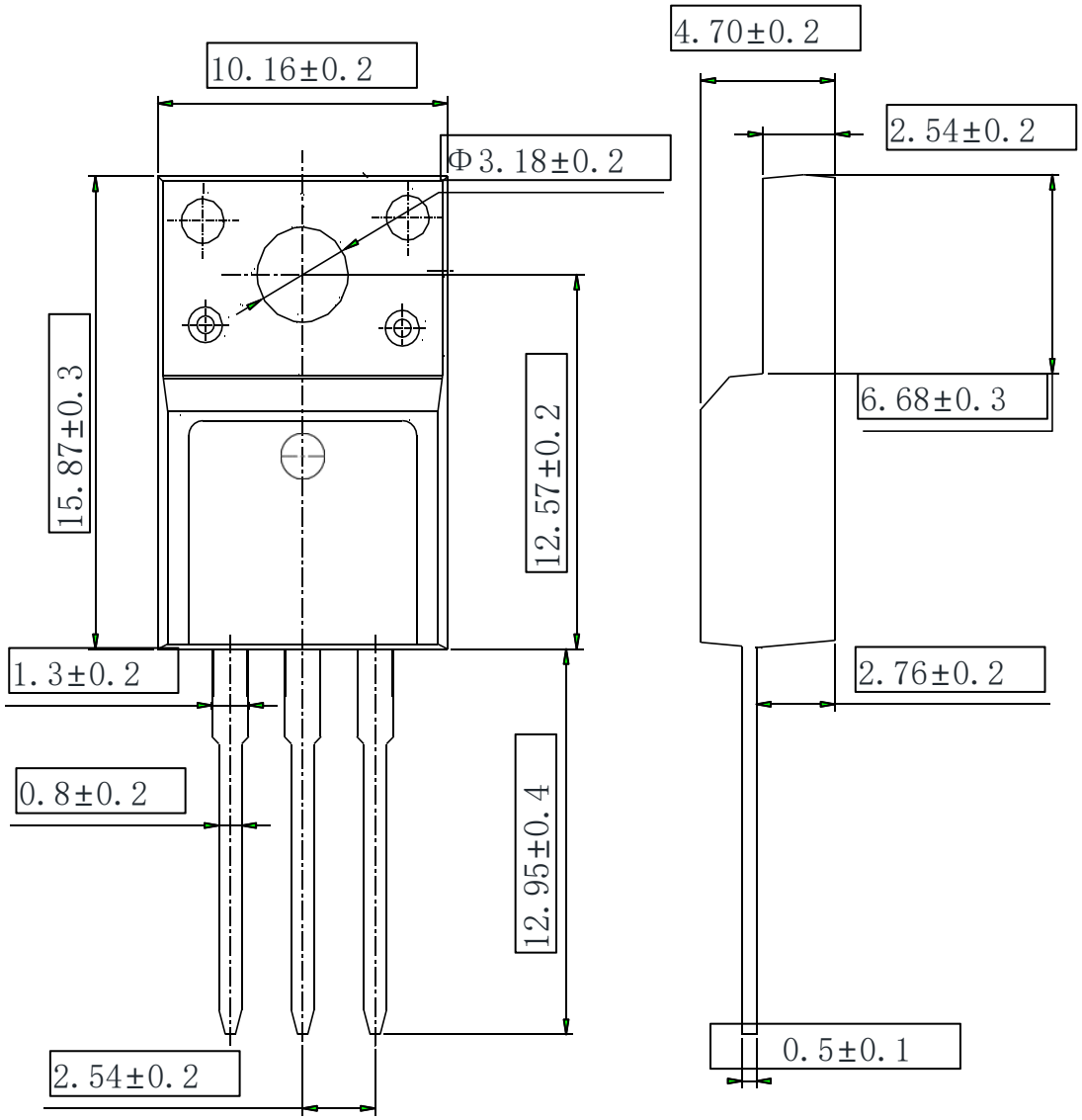




TO-220C OUTLINE



TO-220F OUTLINE



NOTE：
1The plastic package is not marked as smooth surfaceRa=0.1;Subglossy surfaceRa=0.8
2.Undeclared tolerance±0.15,Unmarked filletRmax=0.25

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